

Welcome

ADVENTURES IN WAVELENGTH DISPERSIVE X-RAY FLUORESCENCE (WDXRF): FLEXIBLE ELEMENT ANALYSIS FOR THIN FILMS AND MORE

SPEAKER:

Meredith Beebe Semiconductor X-ray Metrology Specialist, Rigaku

January 27, 2022 | 11am PT





COVALENT ACADEMY

Advancements in Instrumentation Series

Episode 29





Silicon Valley-based analytical labs and platform delivering quality data and expert analysis for advanced materials and device innovation



Covalent Technical Groups and Organization



PCBA, Semiconductor, and Electronic Device Metrology & Failure Analysis	Electron Microscopy and Scanning Probe Microscopy	Optical Microscopy & Spectroscopy	X-Ray Characterization
 DPA / Mechanical Cross-section Dye & Pry Test EBIC / OBIC failure analysis Hot Spot Detection IR Imaging / Emission Microscopy NIR Imaging Root-Cause Failure Analysis 	 AFM & Advanced AFM Modes (EFM, KPFM, MFM, PFM) Scanning Acoustic Microscopy (SAM) SEM (+ EDS) FIB-SEM (+ EDS) S/TEM (+ EDS / + EELS) Nano-indent / Nano-scratch 	 Chromatic Aberration Digital Optical Microscopy FTIR and ATR-FTIR Laser Scanning Confocal Microscopy Spectral Ellipsometry UV-Vis-NIR Spectroscopy White Light Interferometry 	 X-Ray Diffraction (XRD) X-Ray Reflectometry (XRR) Micron-spot ED-XRF WDXRF Micro-computed X-ray Tomography (Micro-CT) 2D X-ray Inspection & X-ray Radiography
Elemental / Chemical Composition Analysis	Particle Analysis	Material Property Characterization	Surface Spectroscopy Analysis
 EPMA GD-OES GC-MS ICP-MS and LA-ICP-MS Raman Microscopy & Spectroscopy NMR (1D or 2D; solid / liquid) 	 Dynamic Light Scattering (DLS) Laser Diffraction Particle Size Analysis (PSA) Particle Zeta Potential 	 DSC DMA & TMA Rheometry TGA Surface Zeta Potential Porometry / Porosity Gas Adsorption Gas Pycnometry Foam Density Tap Density 	 Dynamic-SIMS ToF-SIMS (Static-SIMS) Ion Scattering Spectroscopy (ISS) Ultraviolet Photoelectron Spectroscopy (UPS) X-ray Photoelectron Spectroscopy (XPS)

Covalent Partners





- Partnership announced Fall, 2018
- Covalent is home to Rigaku's
 Silicon Valley Semiconductor Division Metrology Lab:
 - SmartLab XRD / XRR with full set of optics + heated stage
 - CT Lab HX 130 X-ray Micro-CT
 - AZX 400 WDXRF with 200 mm and 300 mm cassettes / FOUP (in clean booth)



Scientific

Introducing



Meredith Beebe

Semiconductor X-ray Metrology Specialist, Rigaku

- Over 20 years in semiconductor industry spanning roles both as an end user in the fab (as a process characterization engineer) and as an applications expert for multiple vendors
- Subject matter expert known across the industry for trace metal and contamination analyses employing X-rays, VPD-ICP-MS, SIMS, AFM, and Auger
- Provides a platform to address ever-changing metrology demands for yield improvement and advanced device development
- Helps Rigaku customers to understand and develop improved strategies for contamination monitoring, metrology optimization, and she provides key insights from direct customer experience to contribute to Rigaku's leadership in X-ray metrology



OUTLINE

- WDXRF technique overview
 - Principles of X-ray fluorescence
 - Sequential and simultaneous spectrometers
 - Qualitative and quantitative methods
 - Comparison of WDXRF to EDXRF
- Rigaku AZX 400 spectrometer overview
- Application studies
 - PZT

Rigaku

- Sputtering target
- MRAM
- Summary/Q&A



FLEXIBILITY OF RIGAKU'S AZX 400 WDXRF

- Non-destructive detection of a wide range of elements from Be-U
 - Example application– MRAM
 - Particularly suited to light elements such as boron through aluminum
 - Ultra-thin MgO film @ 1 nm
- Flexible sample handling supporting enterprise needs from process R&D to manufacturing
 - Example application– Sputtering target
 - Multiple sample adaptors allow for various shapes and sizes of coupons, targets, and wafer samples
 - Sample size range up to 380 mm
- Film thickness measurements from angstroms to microns
 - Example application– PZT
 - High-precision measurements





BASIC PRINCIPLES OF X-RAY FLUORESCENCE



X-ray (high-energy photon) is directed at the sample.

Incident X-ray with sufficient energy ejects an electron from an atom leaving a vacancy.

This vacancy puts the atom in an unstable excited state with a higher energy.



Atom relaxes to restore to its original configuration. It transfers an electron from an outer shell to the lower energy level to fill vacancy.

The replacing electron loses energy, which is radiated as X-rays of a characteristic energy.

The intensity of fluorescent X-ray photons is proportional to a given element.





SEQUENTIAL WDXRF



Sequential spectrometers use a moving detector on a goniometer to move through an angular range to measure the intensities of many different wavelengths.



SIMULTANEOUS WDXRF



Simultaneous spectrometers are equipped with a set of fixed detection systems, where each system measures the radiation of a specific element.



QUALITATIVE SCANS



Non-quantitative scans of elements across the periodic table can be set up to identify elements present in the sample



FILM THICKNESS AND X-RAY INTENSITY

Film thickness is obtained by calibration based on the relationship between thickness and X-ray intensity.





QUANTITATIVE METHODS

Standardization models to address thin film and bulk samples

- Fundamental parameter (FP)
 - Pure element or "type standards"- quantitative
 - Type standards are similar in composition to "unknowns" to be measured
 - Improves accuracy of FP calibration
 - Library standards– semi-quantitative
 - Computer-stored calibration parameters
 - Helpful when calibration standards are not available
 - Density is important for determining linear thickness
- Empirical models
 - Relies on a suite of calibration standards covering the range and thickness values expected of "unknown" product



FP AND EMPIRICAL CALIBRATIONS



- Theoretical vs measured intensity
- Theoretically linear
- Thickness and composition analysis can be done simultaneously with multiple layers
- Few standards are enough, pure metals can be used



- Measured intensity vs standard value
- Not usually linear
- Analyzes only thickness or composition
- Range of standards necessary for each element, thickness, and composition



WDXRF AND EDXRF COMPARISON





RESOLUTION COMPARISON OF WDXRF AND EDXRF

1 µm Al film



WDXRF can clearly resolve the Al-Ka peak (1.487 keV) without influence from the substrate Si-Ka peak (1.740 keV).



RESOLUTION COMPARISON OF WDXRF AND EDXRF

GST film with Ge, Sb, and Te



Clear separation of Sb-La (3.606 keV) and Te-La (3.770 keV) peaks in GST film with WDXRF.



SEQUENTIAL WAVELENGTH DISPERSIVE XRF RIGAKU AZX 400



- 4 kW sealed X-ray tube, sequential type goniometer, primary beam filter; Measurement spot sizes 30, 20, 10, 1, and 0.5 mm in diameter
- Flexibility to measure a variety of sample types, including 50 - 300 mm wafers, coupons, and sputtering targets. Auto wafer loader option available.
- Analyzes elements from Be to U with a range from ppm to % or thickness range of Å to μm
- Well-suited for process R&D and low-volume, high product mix environments
- SEMI and CE compliant with a small footprint, 1376 (W) x 1710 (H) x 890 (D) mm



3 DIFFERENT APPLICATIONS OF WDXRF

- MRAM
- Sputtering target
- PZT







APPLICATION 1: MRAM

Magnetoresistive random access memory

- MRAM is a non-volatile random-access memory which stores data in magnetic domains.
- Faster writing speeds and re-writing times than flash memory.
- MRAM basic structure is a magnetic tunnel junction (MTJ).



MTJ structure consists of two ferromagnetic (FM) layers separated by an insulating tunnel barrier.



APPLICATION 1: MRAM





• Thickness and composition monitoring of each layer are necessary quality controls for manufacturing.



ANALYSIS OF MgO LAYER

Ta layer is often used as a cap and/or barrier around the MTJ structure.

In this case, the Ta-Ma peak that is near Mg-Ka (1.254 keV) is fully resolved.

With EDXRF, the Mg-Ka peak can overlap with the high background of Si-Ka (1.74 keV) and Ta-Ma (1.77 keV).





ANALYSIS RESULTS OF MgO LAYER



10 times measurement of each sample

	MgO Thickness						
Target Thickness	0.4	0.8	1.2	1.6			
Unit	Nm						
Data No.	10	10	10	10			
AVERAGE	0.40	0.80	1.20	1.60			
MAX	0.40	0.81	1.21	1.61			
MIN	0.39	0.80	1.20	1.60			
RANGE	0.01	0.01	0.01	0.01			
Std. Dev.	0.0035	0.0042	0.0046	0.0052			
R.S.D. (%)	0.88	0.52	0.39	0.32			

WDXRF FP calibration of ultra-thin Mg thickness range from 4-16 Å.

This technique can see 1 Å steps and ultra-thin thicknesses of 5 Å, which can be difficult for other methods.



APPLICATION 2: SPUTTERING TARGET ANALYSIS

- Sputtering targets are used to create thin films in sputter deposition tools.
- Composition and trace element detection is important to manufacturers.
- Stoichiometry of target composition can change with use



Good adventure for WDXRF

- Non-destructive and no sample prep needed for analysis



- Wide elemental range (Be-U) for various sputtering target materials
- Library standards can be used if standards are not readily available
 - AZX 400 can accommodate large target samples or wafer samples from sputter target deposition



TARGET QUALITATIVE SCAN



Huge peaks are observed for Pb, Zr, and Ti dominant elements.

AZX 400 primary filters are used in analysis to suppress the background and high Xray intensity for these elements and avoid counting loss errors for Pb and Zr.

This target also had trace amounts of Si and Al.



TARGET REPEATABILITY MEASUREMENT

Component	PbO	ZrO2	TiO2	SiO2	Al2O3	Element Spectrum	Pb La	Zr Ka	Ti Ka	Al Ka	Si Ka
	Comp.	Comp.	Comp.	Comp.	Comp.	kV-mA 50kV – 60mA		۱A	30kV – 100mA		
Unit	mol%	mol%	mol%	mol%	mol%	Primary Filter	*F-Cu	*F-Cu	*E-Sn	OUT	OUT
Data No.	10	10	10	10	10	Diameter			20 mm		
AVERAGE	54.798	23.407	21.659	0.087	0.050	Slit	S2	S2	S2	S4	S4
MAX.	54.849	23.438	21.722	0.089	0.053	Analyzing Crystal	LiF1	LiF1	LiF1	PET	PET
MIN.	54.758	23.373	21.575	0.082	0.048	Detector	SC	SC	SC	F-PC	F- PC
RANGE	0.091	0.065	0.147	0.007	0.005	Counting	ounting	10	10	20	
Std. Dev.	0.025	0.023	0.041	0.002	0.002	Peak	10	10	10	20	20
R.S.D.(%)	0.05	0.10	0.19	2.65	3.05	Background	5	5	5	10	10

Table: 10 times measurement of center point

*Usually, primary filters are used to reduce the diffraction interference, but for this measurement they were used to reduce background and high intensity.



PbO ZrO2 TiO2 SiO2 AI2O3 Component Comp. Comp. Comp. Comp. Comp. Unit mol% mol% mol% mol% mol% Data No. 25 25 25 25 25 **AVERAGE** 54.782 23.427 21.654 0.085 0.053 MAX. 54.888 23.480 21.860 0.112 0.099 MIN. 54.620 23.353 21.501 0.065 0.040 RANGE 0.268 0.127 0.359 0.047 0.059 Std. Dev. 0.090 0.064 0.034 0.013 0.011

Table: 25-point mapping test

0.41

15.49

19.96

0.14

0.12





Maps of the trace SiO2 (mol%) and Al2O3 (mol%) detected

Rigaku

R.S.D.(%)

APPLICATION 3: PZT, LEAD ZIRCONATE TITANATE (Pb[Zr(x)Ti(1-x)]03)

- Piezo-electric material is in various sensors and MEMS devices in ink-jet printers, gyroscopes, mirrors for wearable devices, and more.
- Both the PZT thickness and composition are critical to device performance.



Good adventure for WDXRF



High spectral resolution needed to separate Pb, Pt, Ti overlapping peaks



FP analysis can analyze complicated multilayer stacks for film thickness and composition



AZX 400 can accommodate PZT wafer samples, coupons, and pure metal disc standards



PZT ANALYSIS WITH WDXRF

• FP analysis allows for TiOx layer thickness to be a fixed value.

This enables Ti to be measured and accounted for from the PZT layer.

• Pure metal standards of Pb, Zr, and Ti can also be used.

PZT (PbO, ZrO2, TiO2)
Pt
Ti (TiOx): Fixed Value
SiO2 : Fixed Value
Si substrate



QUALITATIVE CHART OF PZT SAMPLE



1 µm PZT and 100 nm Pt spectra.

WDXRF high spectral resolution resolves the Pb-L line, Pt-L line, and Zr-K line that overlap each other in EDXRF.



PZT ANALYSIS RESULTS

Layer	PZT							
Component	Thk.	PbO Conc.	ZrO2 Conc.	TiO2 Conc.	Pb / (Zr+Ti)	Zr / (Zr+Ti)	Thk.	
Unit	nm	mol%	mol%	mol%	-	-	nm	
AVERAGE	3282.1	49.42	26.27	24.31	0.977	0.519	100.0	
MAX.	3288.7	49.48	26.35	24.38	0.979	0.521	100.2	
MIN.	3272.3	49.37	26.19	24.23	0.975	0.518	99.7	
RANGE	16.4	0.11	0.15	0.15	0.004	0.003	0.5	
Std. Dev.	4.7	0.034	0.041	0.052	0.0013	0.0009	0.15	
R.S.D.(%)	0.14	0.07	0.16	0.21	0.14	0.17	0.15	

Thickness and composition of the PZT and Pt layer are calculated.

10x repeat thickness measurements <.2% RSDs.

Composition of PbO, ZrO2, TiO2 are calculated.

Pb/(Zr+Ti) and Zr/(Zr+Ti) composition ratios are also determined from measured mol%.

Table: 10 times repeatability measurement of PZT/Pt multilayer

*Measurement from fixed channel WDXRF system



AZX 400 MEASUREMENT FLEXIBILITY

- Different sample adaptors to accommodate a range of sample sizes
- Vacuum option
- Library standards are available for semi-quantitative analysis if standards are not readily available.
- FP method and high peak resolution enable resolution of complicated spectra and overlapping peaks.
- Primary beam filters diffraction elimination







WDXRF THIN FILM APPLICATIONS

• Semiconductor films

Doped poly-Si (B, P, C, N, As), SiGe

• Insulative films

Insulator film:
Low-k film:
Nitride film:
High-k film:

PSG, BPSG AsSG, FSG SiOC Si₃N₄, SiON La₂O₃, HfO₂, Ta₂O₅, Al₂O₃



• Metal, conductive films

Metal alloy film: Metal film: Silicide film: Nitride film (Barrier):

• Other

Power Device: Universal Memory: MEMS (piezo, mobile): Other Purposes: AlSiCu, AlCu, TiW, TaAl W, Mo, Ti, Co, Al, Cu, Ir, Pt, Ru WSix, MoSix, TiSix, CoSix, NiSix TiN, TaN, WN

Au(Ag)/Ni/Ti/Al (backside electrode) MRAM (MgO, CoFeB), GST, PZT PZT, (Sc,Ta)AlN, SAW, F-BAR LED, sputtering target, photomask, F, Cl residue, C film

Ge, Sb, Te (+ Ga, In, N, C) Oxidized layer Si substrate



KEY FEATURES OF WDXRF

- Non-destructive detection for wide range elements from
- Ultra thin film thickness measurements from 0.1 nm
- **High peak resolution** and fundamental parameter (FP) analysis can analyze multilayer stacks with complicated compounds
- Multiple sample adaptors allow for various shapes, coupons, and wafer samples from 50 mm- 380 mm
- Library standards in software provides **semi-quantitative measurement analysis without standards**
- Qualitative measurements scan for smaller element groups or from Be-U





Coming Up...



LASER ABLATION INDUCTIVELY COUPLED PLASMA MASS SPECTROSCOPY: NOT JUST ROCKS

SPEAKER:

Lucas Smith Director of Business Development for the Americas, Teledyne CETAC

February 10, 2022 | 11am PT





COVALENT ACADEMY

Advancements in Instrumentation Series

Episode 30



Want to learn more about Covalent's

WDXRF and Spectroscopy Services?

Talk with a Covalent Expert!

Schedule your Appointment Now with Calendly - link is in the chat -

Covalent Community







Covalent Community



Search Technique or Measurement...

Q



RICING RESOURCES BLOG

Schedule Pickup

I OGIN

Access Covalent Portals

Customer Access to Data & Community Content



The DATA PORTAL is used by Customers and Lab Partners for uploading and downloading data. It requires two-factor authentication and advanced password protection. Data Portal users have complete access through their home page on the portal to all Community content, and do not require a separate Community account.

Community Content Access for All Other Users

Contact Us

ABOUT

COVALENT



The COVALENT COMMUNITY PORTAL requires password entry. It contains webinar and other metrology and characterization-related content that we believe would be useful and educational for the materials science innovation community. It does <u>not</u> provide access to any customer data and should only be used by individuals that are not Covalent customers or lab partners.

LOGIN TO DATA PORTAL

LOGIN TO COMMUNITY PORTAL





Q&A Session

